

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--|------------------|---------|------------------|
| S1 | 298 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 10:18 |
| S2 | 295 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/23 20:08 |
| S3 | 264 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 10:20 |
| S4 | 215 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:18 |

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| S5 | 1 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilsesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) and (onium near8 compound) and nucleophil\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 10:45 |
| S6 | 1 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilsesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) and (onium near8 compound) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 10:46 |

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| S7 | 21 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilsesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 11:14 |
| S8 | 0 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilsesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) and gell | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 11:17 |

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| S9 | 21 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and polymer and catalyst and porogen and (heat or anneal) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 11:18 |
| S11 | 2 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and polymer and catalyst and porogen and (heat or anneal) and (remov\$4 near8 porogen) and onium | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/16 11:19 |

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| S12 | 21 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and polymer and catalyst and porogen and (heat or anneal) and (remov\$4 near8 porogen) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 11:49 |
| S13 | 124 | "5895263" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 11:49 |
| S14 | 76 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and gel\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:21 |

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| S15 | 28 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilsesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and gel\$4 and catalyst | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:22 |
| S16 | 1 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilsesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and gel\$4 and catalyst and onium | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:23 |
| S17 | 1 | (porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and gel\$4 and catalyst and onium | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:24 |
| S18 | 4601 | gel\$4 and catalyst and onium | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:24 |

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| S19 | 1348 | gel\$4 and catalyst and (onium near4 compound) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:25 |
| S20 | 46 | gel\$4 and catalyst and (onium near4 compound) and nucleophile | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:31 |
| S22 | 5 | gel\$4 and catalyst and (onium near4 compound) and nucleophile and polyalkylene and (acetoxysilane or ethoxysilane or methoxysilane) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:34 |
| S23 | 1 | gel\$4 and catalyst and (onium near4 compound) and nucleophile and polyalkylene and (acetoxysilane or ethoxysilane or methoxysilane) and infiltrat\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/17 12:33 |
| S24 | 11 | gel\$4 and catalyst and (onium near4 compound) and nucleophile and polyalkylene | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/21 08:06 |
| S25 | 55165 | (porous near9 (dielectric or oxide or insulat\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/23 20:26 |
| S26 | 9916 | (porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/23 21:03 |

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| S27 | 0 | (porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) and (nonporous near cap) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/23 21:29 |
| S28 | 22 | (porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) and (nonporous near (oxide or dielectric or insulat\$4 or cap)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/23 21:29 |
| S29 | 20 | (porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) and (nonporous near (oxide or dielectric or insulat\$4 or cap)) and (substrate or wafer or carrier or base) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/06/23 21:31 |